Abstract Submitted
for the MAR10 Meeting of
The American Physical Society

FET device with suspended graphene JIAN MING LU, ZI KANG TANG — Because of its linear electronic dispersion, graphene has been intensively studied for electronic application. Top-gated FET device has been measured [1]. Here we study the FET with high quality suspended graphene under high source-drain bias voltage. In addition, two-dimensional temperature distribution of the whole device has been detected by the Raman shift of its 2D peak around 2700cm^{-1}.

[1] Inanc Meric et al. *Nature Nanotechnology* **3**, 654 - 659 (2008).

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Date submitted: 22 Nov 2009 Electronic form version 1.4